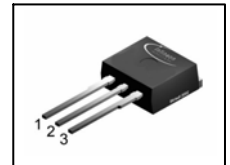


**Cool MOS™ Power Transistor**
**Feature**

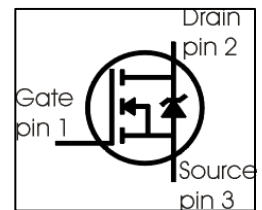
- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme  $dv/dt$  rated
- High peak current capability
- Intrinsic fast-recovery body diode
- Extreme low reverse recovery charge
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>0)</sup> for target applications

$V_{DS} @ T_{jmax}$	650	V
$R_{DS(on)}$	0.44	$\Omega$
$I_D$	11	A

PG-TO262



Type	Package	Pb-free	Marking
SPI11N60CFD	PG-TO220	Yes	11N60CFD


**Maximum Ratings**

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25\text{ °C}$ $T_C = 100\text{ °C}$	$I_D$	11 7	A
Pulsed drain current, $t_p$ limited by $T_{jmax}$	$I_{D\text{ puls}}$	28	
Avalanche energy, single pulse $I_D = 5.5\text{ A}$ , $V_{DD} = 50\text{ V}$	$E_{AS}$	340	mJ
Avalanche energy, repetitive $t_{AR}$ limited by $T_{jmax}$ <sup>1)</sup> $I_D = 11\text{ A}$ , $V_{DD} = 50\text{ V}$	$E_{AR}$	0.6	
Avalanche current, repetitive $t_{AR}$ limited by $T_{jmax}$	$I_{AR}$	11	A
Reverse diode $dv/dt$ $I_S = 11\text{ A}$ , $V_{DS} = 480\text{ V}$ , $T_j = 125\text{ °C}$	$dv/dt$	40	V/ns
Gate source voltage	$V_{GS}$	$\pm 20$	V
Gate source voltage AC ( $f > 1\text{ Hz}$ )	$V_{GS}$	$\pm 30$	
Power dissipation, $T_C = 25\text{ °C}$	$P_{tot}$	125	W
Operating and storage temperature	$T_j, T_{stg}$	-55... +150	$\text{°C}$

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Drain Source voltage slope $V_{DS} = 480\text{ V}$ , $I_D = 11\text{ A}$ , $T_j = 125\text{ °C}$	$dv/dt$	80	V/ns
Maximum diode commutation speed $V_{DS} = 480\text{ V}$ , $I_D = 11\text{ A}$ , $T_j = 125\text{ °C}$	$di/dt$	600	A/ $\mu$ s

**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	$R_{thJC}$	-	-	1	K/W
Thermal resistance, junction - ambient, leaded	$R_{thJA}$	-	-	62	
Soldering temperature, wavesoldering 1.6 mm (0.063 in.) from case for 10s	$T_{sold}$	-	-	260	$^{\circ}\text{C}$

**Electrical Characteristics, at  $T_j=25^{\circ}\text{C}$  unless otherwise specified**

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{V}$ , $I_D=0.25\text{mA}$	600	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{V}$ , $I_D=11\text{A}$	-	700	-	
Gate threshold voltage	$V_{GS(th)}$	$I_D=500\mu\text{A}$ , $V_{GS}=V_{DS}$	3	4	5	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=600\text{V}$ , $V_{GS}=0\text{V}$ , $T_j=25^{\circ}\text{C}$ , $T_j=150^{\circ}\text{C}$	-	1.1	-	$\mu\text{A}$
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{V}$ , $V_{DS}=0\text{V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}$ , $I_D=7\text{A}$ , $T_j=25^{\circ}\text{C}$ $T_j=150^{\circ}\text{C}$	-	0.38	0.44	$\Omega$
Gate input resistance	$R_G$	$f=1\text{MHz}$ , open Drain	-	0.86	-	

**Electrical Characteristics** , at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Transconductance	$g_{fs}$	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = 7\text{A}$	-	8.3	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$	-	1200	-	pF
Output capacitance	$C_{oss}$		-	390	-	
Reverse transfer capacitance	$C_{rss}$		-	30	-	
Effective output capacitance, <sup>2)</sup> energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 0\text{V to } 480\text{V}$	-	45	-	pF
Effective output capacitance, <sup>3)</sup> time related	$C_{o(tr)}$		-	85	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 380\text{V}$ , $V_{GS} = 0/10\text{V}$ , $I_D = 11\text{A}$ , $R_G = 6.8\Omega$	-	34	-	ns
Rise time	$t_r$		-	18	-	
Turn-off delay time	$t_{d(off)}$		-	43	-	
Fall time	$t_f$		-	7	-	

**Gate Charge Characteristics**

Gate to source charge	$Q_{gs}$	$V_{DD} = 480\text{V}$ , $I_D = 11\text{A}$	-	9	-	nC
Gate to drain charge	$Q_{gd}$		-	23	-	
Gate charge total	$Q_g$	$V_{DD} = 480\text{V}$ , $I_D = 11\text{A}$ , $V_{GS} = 0\text{ to } 10\text{V}$	-	48	64	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 480\text{V}$ , $I_D = 11\text{A}$	-	7	-	V

<sup>0</sup>J-STD20 and JESD22

<sup>1</sup>Repetitive avalanche causes additional power losses that can be calculated as  $P_{AV} = E_{AR} \cdot f$ .

<sup>2</sup> $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

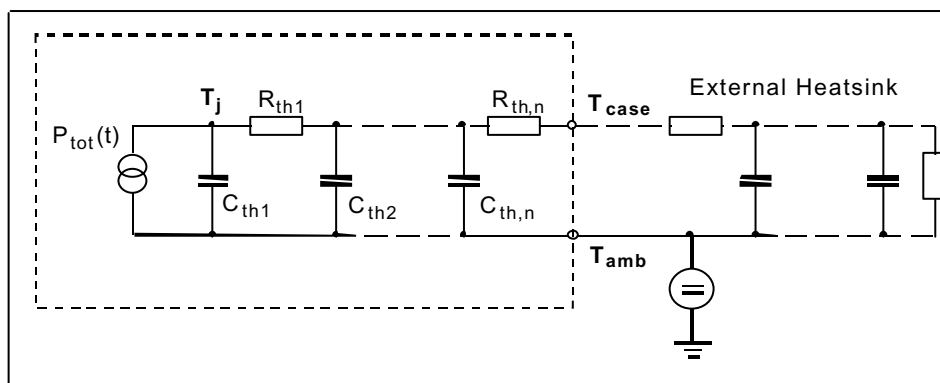
<sup>3</sup> $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

**Electrical Characteristics, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	$I_S$	$T_C=25^\circ\text{C}$	-	-	11	A
	$I_{SM}$		-	-	28	
Inverse diode forward voltage	$V_{SD}$	$V_{GS}=0\text{V}, I_F=I_S$	-	1	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=480\text{V}, I_F=I_S,$ $di_F/dt=100\text{A}/\mu\text{s}$	-	140	-	ns
Reverse recovery charge	$Q_{rr}$		-	0.7	-	$\mu\text{C}$
Peak reverse recovery current	$I_{rrm}$		-	11	-	A
Peak rate of fall of reverse recovery current	$di_{rr}/dt$		-	1200	-	$\text{A}/\mu\text{s}$

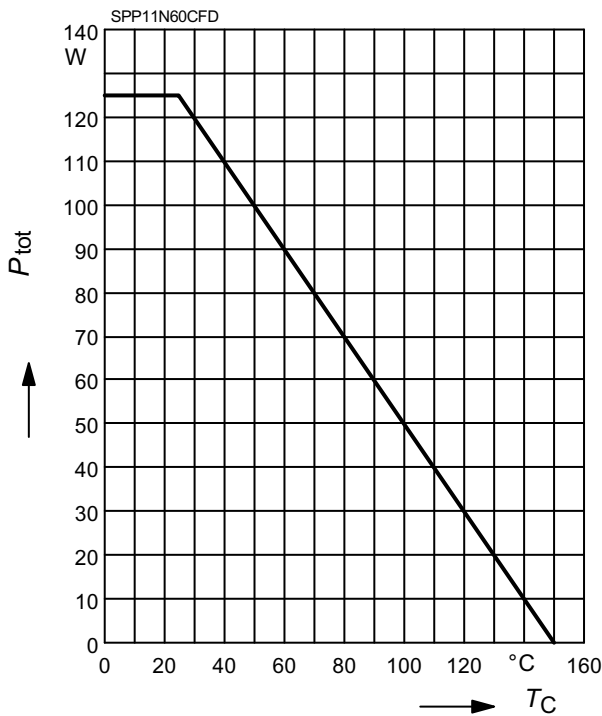
**Typical Transient Thermal Characteristics**

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
Thermal resistance			Thermal capacitance		
$R_{th1}$	0.015	K/W	$C_{th1}$	0.0001878	Ws/K
$R_{th2}$	0.03		$C_{th2}$	0.0007106	
$R_{th3}$	0.056		$C_{th3}$	0.000988	
$R_{th4}$	0.197		$C_{th4}$	0.002791	
$R_{th5}$	0.216		$C_{th5}$	0.007285	
$R_{th6}$	0.083		$C_{th6}$	0.063	



### 1 Power dissipation

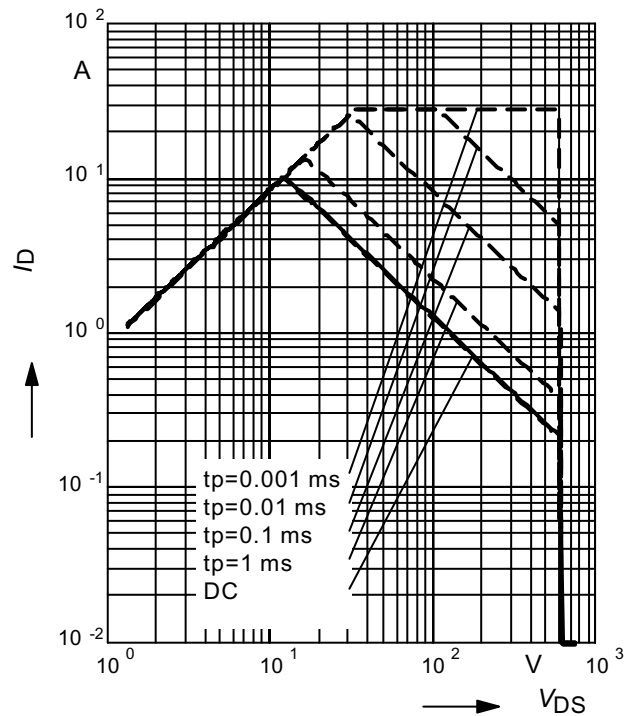
$$P_{tot} = f(T_C)$$



### 2 Safe operating area

$$I_D = f(V_{DS})$$

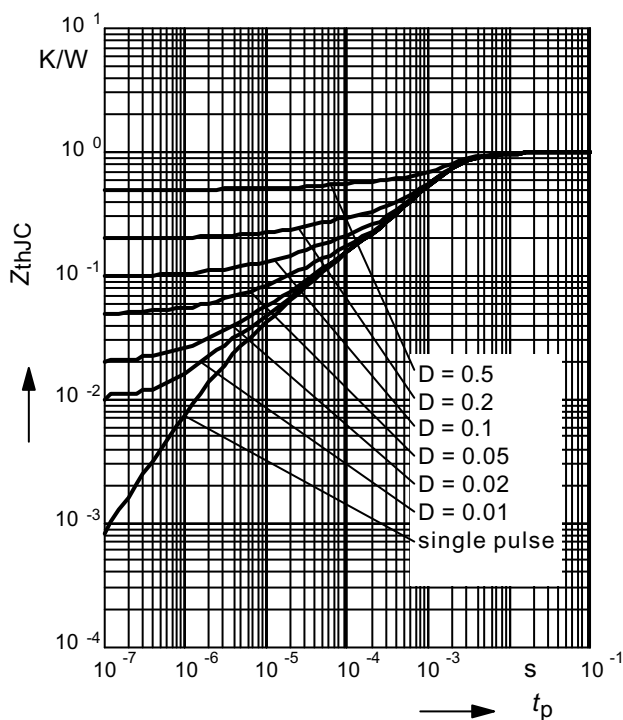
parameter :  $D = 0, T_C = 25^\circ\text{C}$



### 3 Transient thermal impedance

$$Z_{thJC} = f(t_p)$$

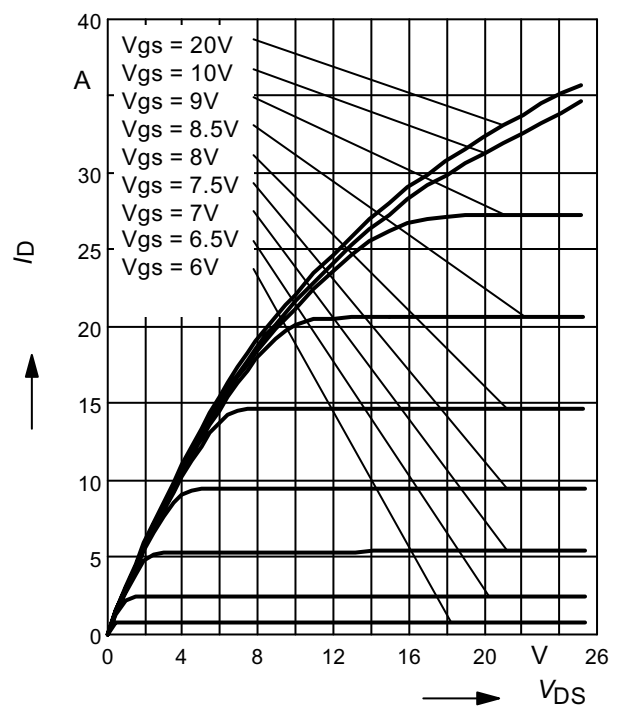
parameter:  $D = t_p/T$



### 4 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

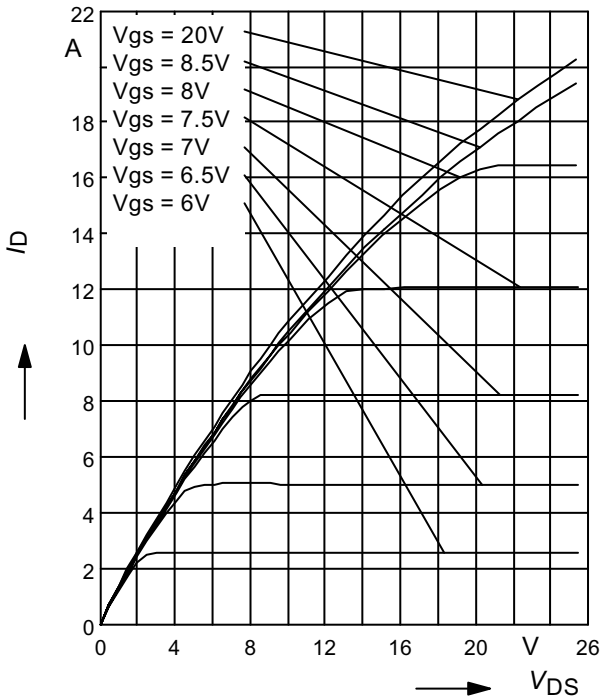
parameter:  $t_p = 10 \mu\text{s}, V_{GS}$



**5 Typ. output characteristic**

$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$

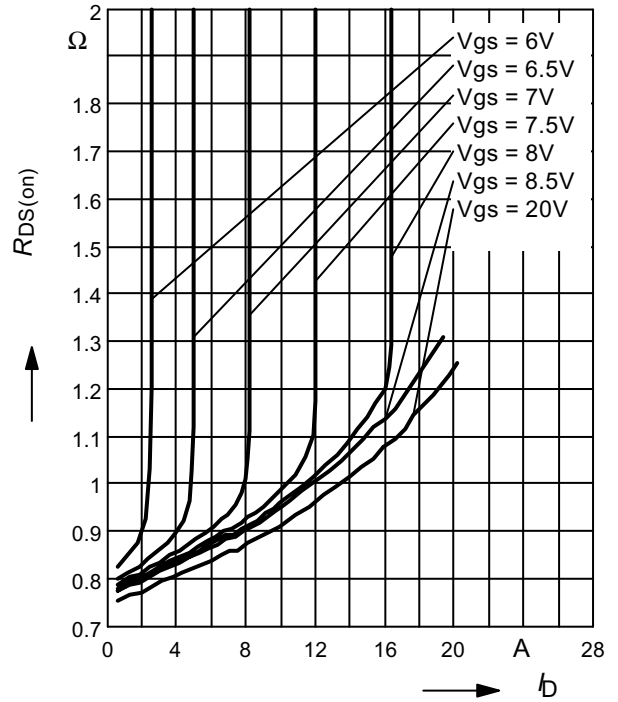
parameter:  $t_p = 10 \mu\text{s}$ ,  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D)$

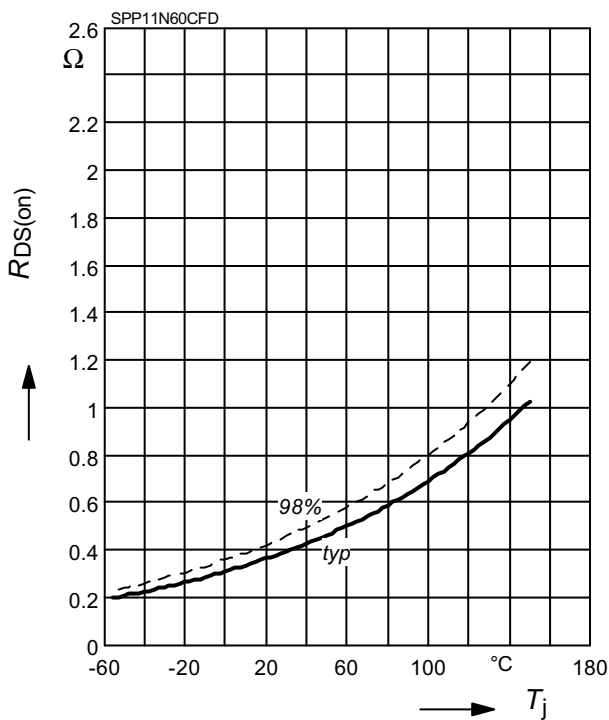
parameter:  $T_j = 150^\circ\text{C}$ ,  $V_{GS}$



**7 Drain-source on-state resistance**

$R_{DS(on)} = f(T_j)$

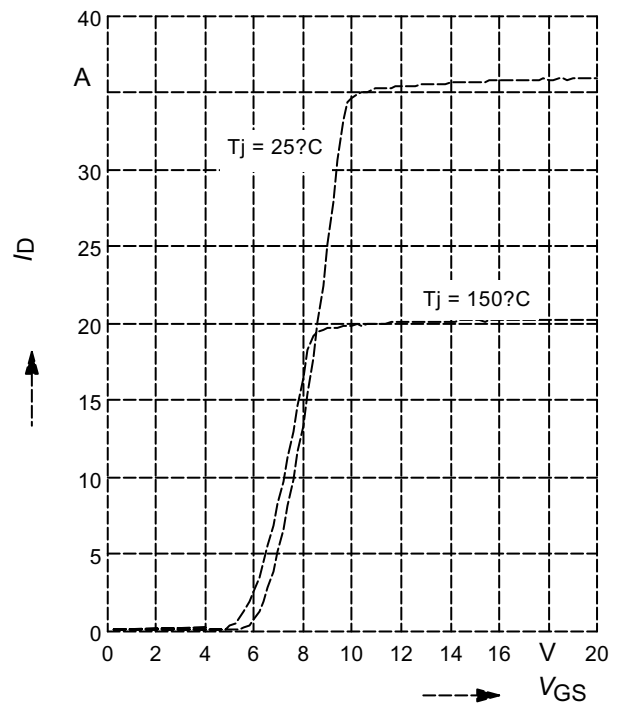
parameter:  $I_D = 7 \text{ A}$ ,  $V_{GS} = 10 \text{ V}$



**8 Typ. transfer characteristics**

$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

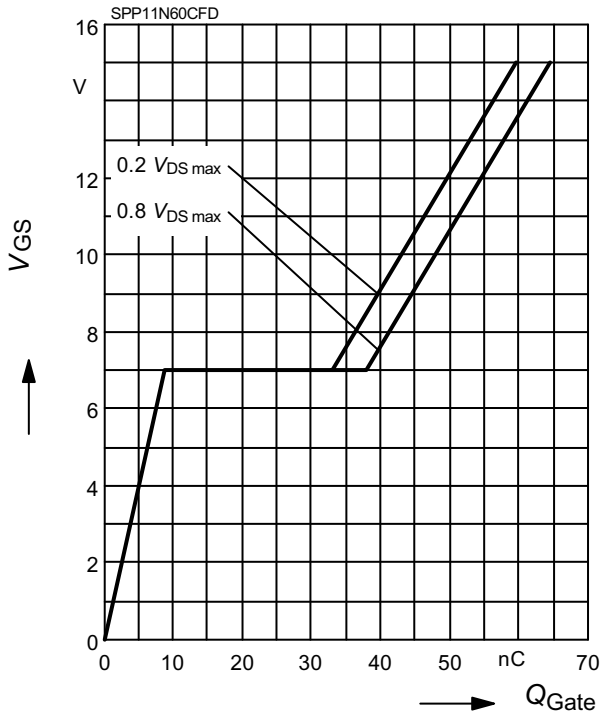
parameter:  $t_p = 10 \mu\text{s}$



**9 Typ. gate charge**

$V_{GS} = f(Q_{Gate})$

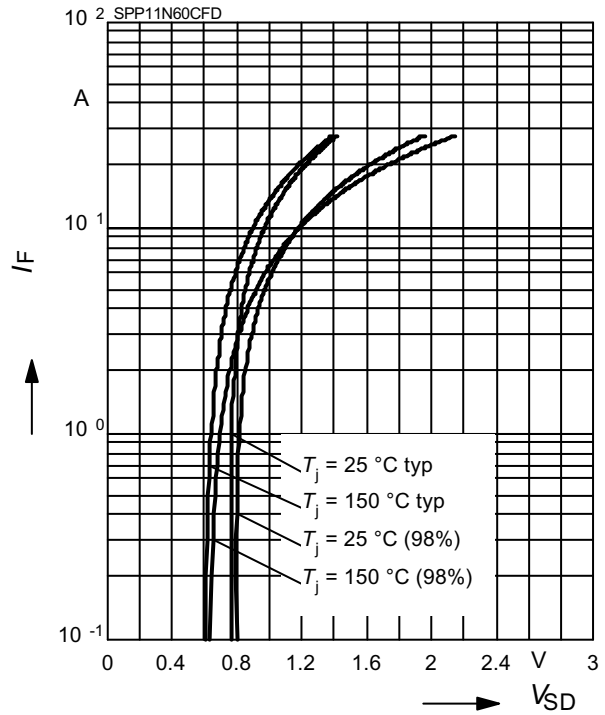
parameter:  $I_D = 11\text{ A}$  pulsed



**10 Forward characteristics of body diode**

$I_F = f(V_{SD})$

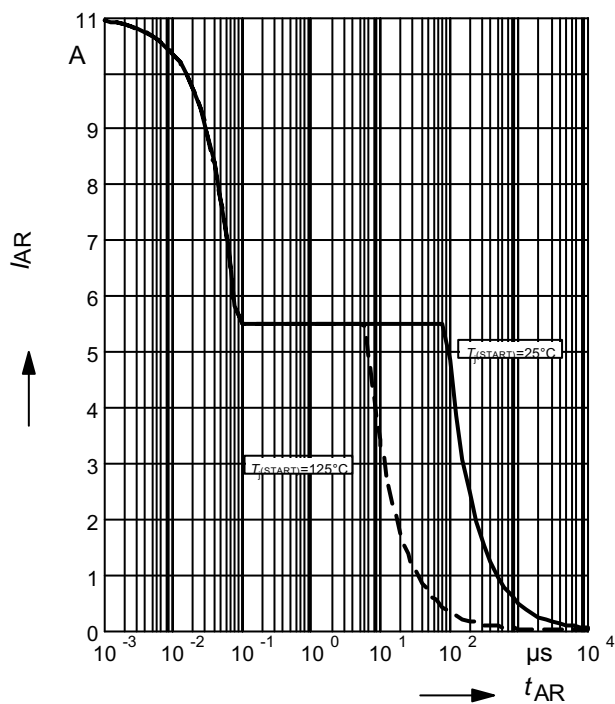
parameter:  $T_j, t_p = 10\ \mu\text{s}$



**11 Avalanche SOA**

$I_{AR} = f(t_{AR})$

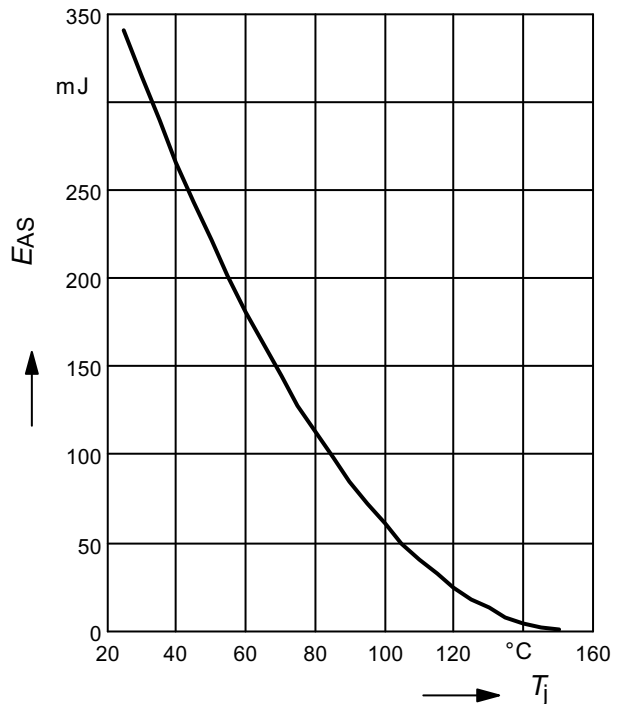
par.:  $T_j \leq 150\ \text{°C}$



**12 Avalanche energy**

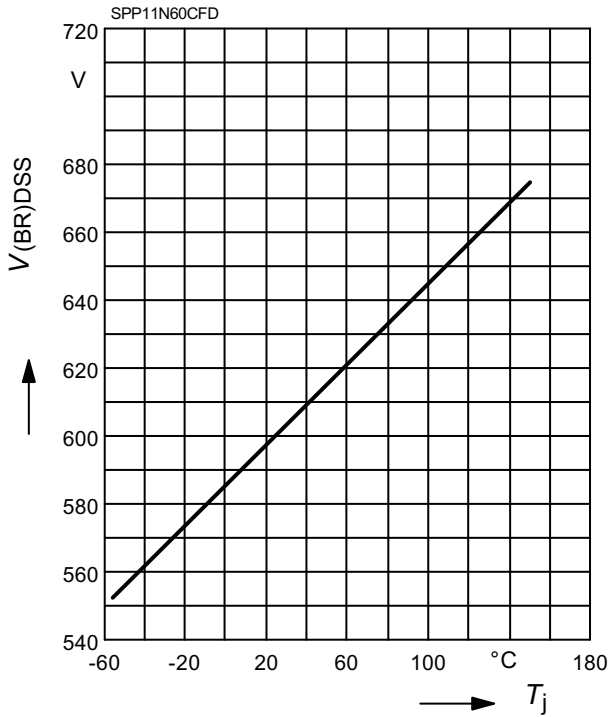
$E_{AS} = f(T_j)$

par.:  $I_D = 5.5\text{ A}, V_{DD} = 50\text{ V}$



**13 Drain-source breakdown voltage**

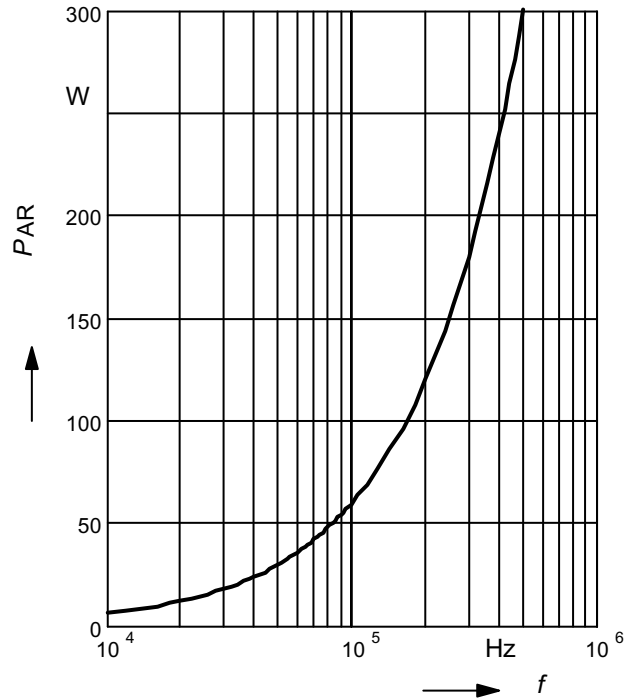
$$V_{(BR)DSS} = f(T_j)$$



**14 Avalanche power losses**

$$P_{AR} = f(f)$$

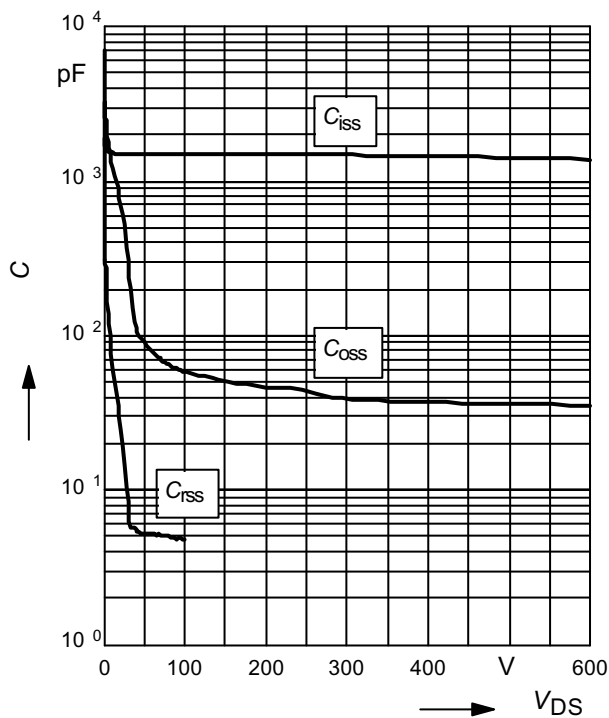
parameter:  $E_{AR}=0.6mJ$



**15 Typ. capacitances**

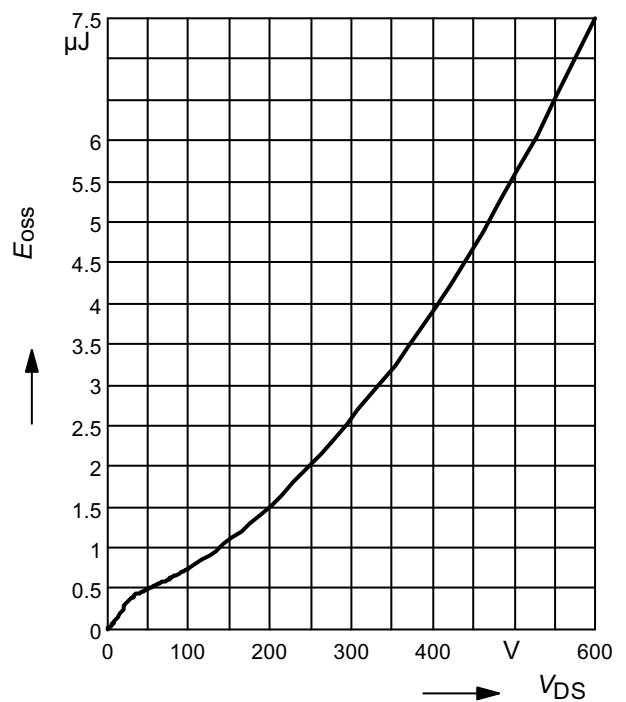
$$C = f(V_{DS})$$

parameter:  $V_{GS}=0V, f=1\text{ MHz}$



**16 Typ.  $C_{OSS}$  stored energy**

$$E_{OSS} = f(V_{DS})$$

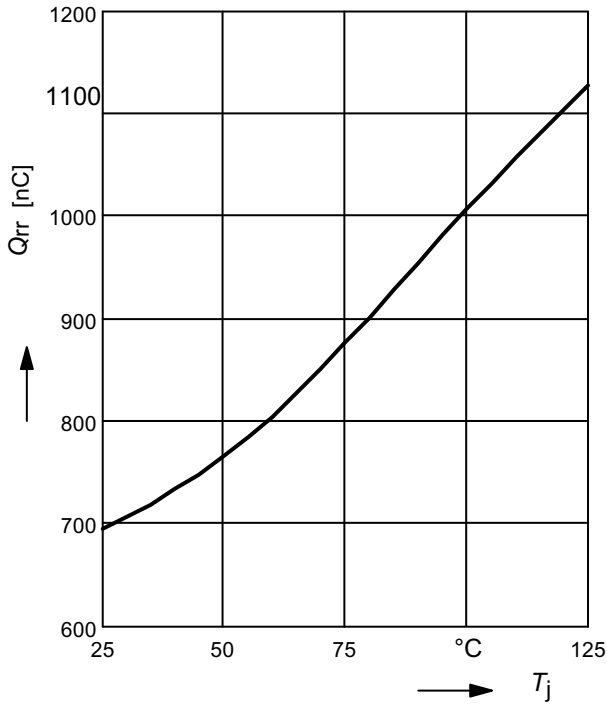




**17 Typ. reverse recovery charge**

$$Q_{rr} = f(T_j)$$

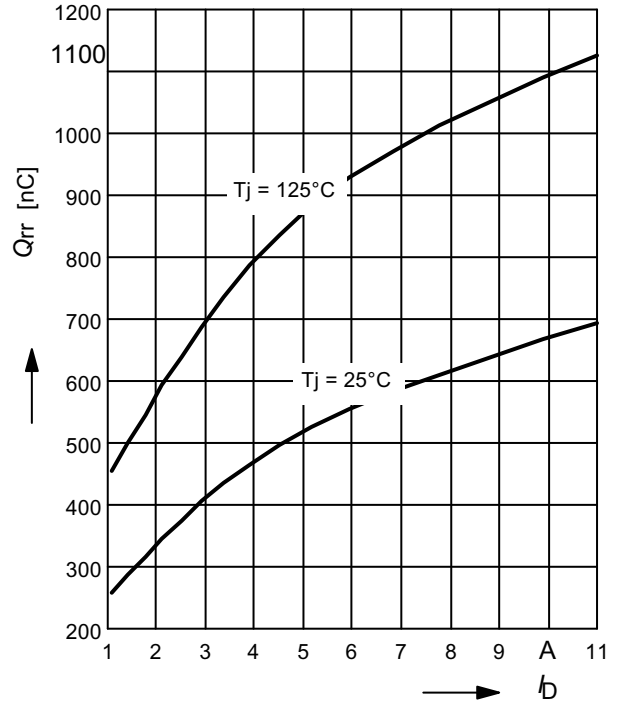
parameter:  $I_D = 11\text{ A}$



**18 Typ. reverse recovery charge**

$$Q_{rr} = f(I_D)$$

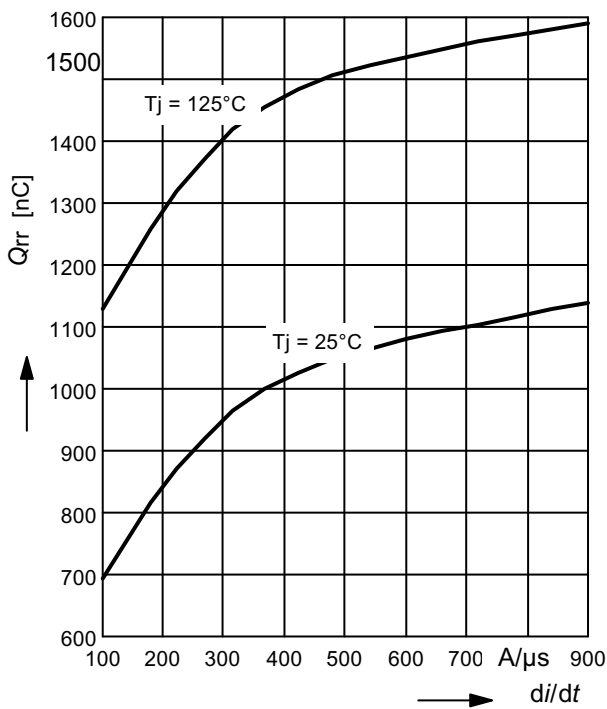
parameter:  $di/dt = 100\text{ A}/\mu\text{s}$



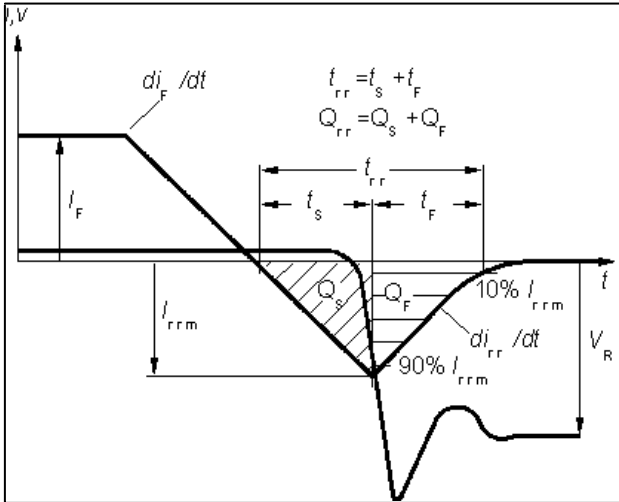
**19 Typ. reverse recovery charge**

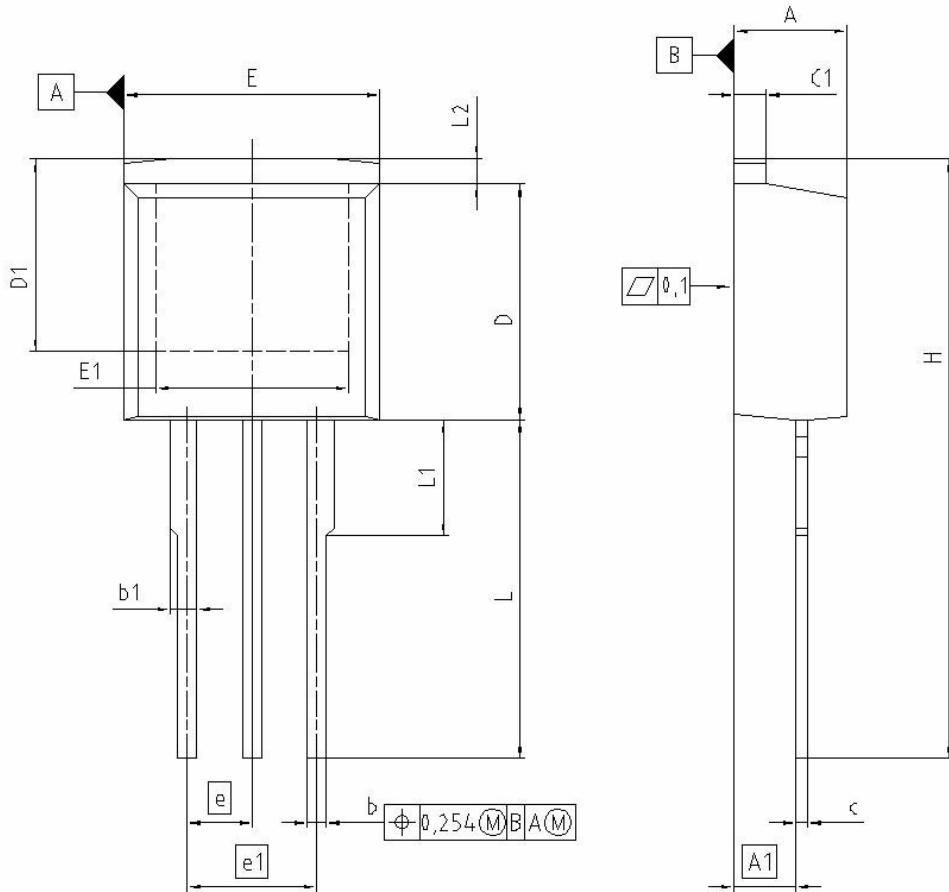
$$Q_{rr} = f(di/dt)$$

parameter:  $I_D = 11\text{ A}$



Definition of diodes switching characteristics

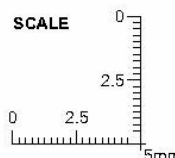




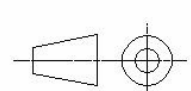
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.300	4.500	0.169	0.177
A1	2.150	2.650	0.085	0.104
b	0.650	0.850	0.026	0.033
b1	0.635	1.400	0.025	0.055
c	0.400	0.600	0.016	0.024
c1	1.170	1.370	0.046	0.054
D	9.050	9.450	0.356	0.372
D1	6.900	7.650	0.272	0.301
E	9.800	10.200	0.386	0.402
E1	7.250	8.600	0.285	0.339
e	2.540		0.100	
e1	5.080		0.200	
N	3		3	
L	13.000	14.000	0.512	0.551
L1	4.350	4.750	0.171	0.187
L2	0.700	1.300	0.028	0.051

**REFERENCE**  
JEDEC TO262

**SCALE**



**EUROPEAN PROJECTION**



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